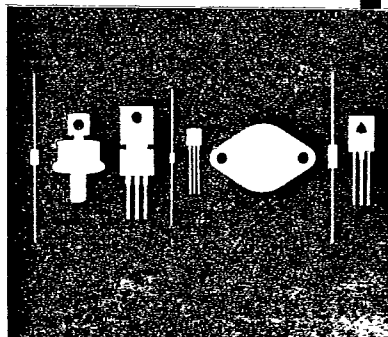


CENTRAL SEMICONDUCTOR

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Central
Semiconductor Corp.Central
Semiconductor Corp.Central
Semiconductor Corp.Central™
Semiconductor Corp.145 Adams Avenue
Hauppauge, New York 117881N5614
1N5616
1N5618
1N5620
1N5622GLASS PASSIVATED RECTIFIER
1.0 AMPS, 200 THRU 1000 VOLTS

GPR-1A CASE

DESCRIPTION

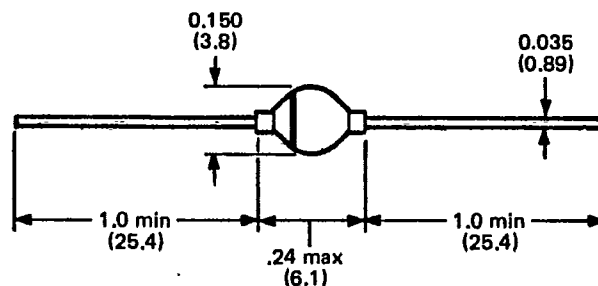
The CENTRAL SEMICONDUCTOR 1N5614 series types are silicon rectifiers mounted in a hermetically sealed, glass passivated package for general applications where high reliability is desired.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	1N5614	1N5616	1N5618	1N5620	1N5622	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V_R	200	400	600	800	1000	V
RMS Reverse Voltage	$V_R(RMS)$	140	280	420	560	700	V
Average Forward Current ($T_A=55^\circ\text{C}$)	I_O			1.0			A
Peak Forward Surge Current	I_{FSM}			50			A
Operating and Storage Junction Temperature	T_J, T_{STG}			-65 TO +200			$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_R	V_R =Rated V_{RRM}		0.5	μA
I_R	V_R =Rated V_{RRM} , $T_A=100^\circ\text{C}$		25	μA
V_F	$I_F=1.0\text{A}$		1.2	V
BVR	$I_R=50\mu\text{A}$ (1N5614)	220		V
BVR	$I_R=50\mu\text{A}$ (1N5616)	440		V
BVR	$I_R=50\mu\text{A}$ (1N5618)	660		V
BVR	$I_R=50\mu\text{A}$ (1N5620)	880		V
BVR	$I_R=50\mu\text{A}$ (1N5622)	1100		V
C	$V_R=12\text{V}$, $f=130\text{kHz}$		35	pF
t_{rr}	$I_F=0.5\text{A}$, $I_R=1.0\text{A}$, Recov. to 0.25A		2.0	μs



DIMENSIONS IN INCHES (MILLIMETERS)